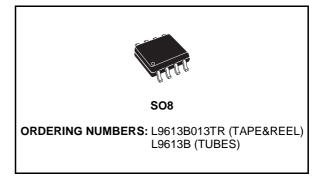


# DATA INTERFACE

- OPERATING POWER SUPPLY VOLTAGE RANGE  $4.8V \le V_S \le 36V$  (40V FOR TRANSIENTS)
- REVERSE SUPPLY (BATTERY) PROTECTED DOWN TO  $V_S \ge -24V$
- STANDBY MODE WITH VERY LOW CURRENT CONSUMPTION IS<sub>SB</sub>  $\leq$  1 $\mu$ A @ V<sub>CC</sub>  $\leq$  0.5V
- MIN POSSIBLE BAUD RATE ACCORDING TO ISO9141 ≥ 130KBAUD
- TTL COMPATIBLE TX INPUT
- BIDIRECTIONAL K-I/O PIN WITH SUPPLY VOLTAGE DEPENDENT INPUT THRESHOLD
- OVERTEMPERATURE SHUT DOWN FUNC-TION SELECTIVE TO K-I/O PIN
- WIDE INPUT AND OUTPUT VOLTAGE RANGE -24V ≤ VK ≤ VS
- KOUTPUT CURRENT LIMITATION, TYP IK = 60mA
- DEFINED OFF OUTPUT STATUS IN UNDER-VOLTAGE CONDITION AND VS OR GND IN-TERRUPTION
- CONTROLLED OUTPUT SLOPE FOR LOW EMI
- HIGH INPUT IMPEDANCE FOR OPEN VS OR GND CONNECTION

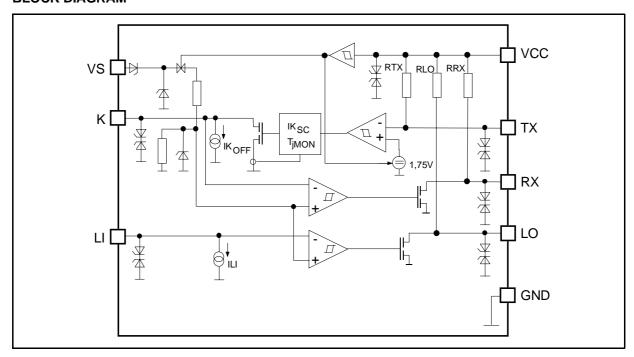


- DEFINED OUTPUT ON STATUS OF LO OR RX FOR OPEN LI OR K INPUTS
- DEFINED K OUTPUT OFF FOR TX INPUT OPEN
- INTEGRATED PULL UP RESISTORS FOR TX, RX AND LO
- EMI ROBUSTNESS OPTIMIZED

#### **DESCRIPTION**

The L9613B is a monolithic integrated circuit containing medium speed data interface functions.

#### **BLOCK DIAGRAM**



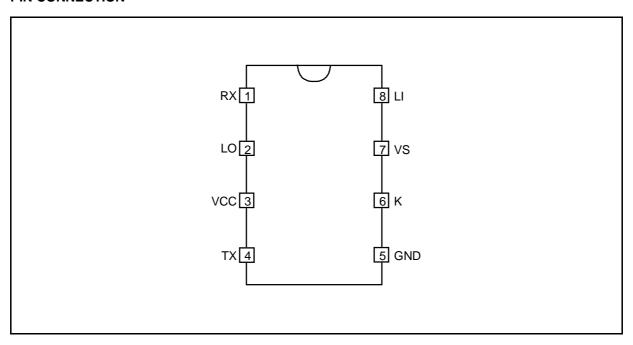
November 1999 1/10

## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vs	Supply Voltage ISO transient t ≤ 400ms	-24 to +36 -24 to +40	V
Vcc	Stabilized Voltage	-24V to 7	V
dV <sub>S</sub> /dt	Supply Voltage Transient	-10 to +10	V/μs
$V_{LI,K}$	Pin voltage	-24 to V <sub>S</sub>	V
V <sub>LO, RX, TX</sub>	Pin voltage	-24 to V <sub>CC</sub>	V

<sup>\*</sup> max ESD voltages are +/-2KV with human body model C=100pF, R=1.5K $\Omega$  corresponds to maximum energy

## **PIN CONNECTION**



## **THERMAL DATA**

Symbol	Parameter	Min.	Тур.	Max.	Unit
T <sub>JSDon</sub>	Temperature shutdown switch-on-threshold	160		200	ç
$T_{JSDoff}$	Temperature shutdown switch-off-threshold	150			ç
R <sub>th(j-a)</sub>	Thermal steady state junction to ambient resistance	130	155	180	°C/W

#### **PIN FUNCTIONS**

N.	Name	Description				
1	RX	Output for K as input				
2	LO	Output L comparator				
3	VCC	Stabilized voltage supply				
4	TX	Input for K as output				
5	GND	Common GND				
6	К	Bidirectional I/O				
7	VS	Supply voltage				
8	LI	Input L comparator				

**ELECTRICAL CHARACTERISTICS** (The electrical characteristics are valid within the below defined Operating Conditions, unless otherwise specified).

The function is guaranteed by design until T<sub>JSDon</sub> temperature shutdown switch-on-threshold.

Vs Supply voltage 4.8 V... 18 V Vcc Stabilized voltage 3 V... 7 V

T<sub>J</sub> Junction temperature -40 °C... 150°C

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Icc	Supply V <sub>CC</sub> Current	$V_{CC} \le 5.5V$ VLI, VTX = 0V		1.4	2.5	mA
		$ \begin{array}{l} VK \geq VK_{high} \\ VLI \geq VLI_{high} \\ VTX = V_{CC} \\ @ \ V_{CC} \leq 5.5V \end{array} $	-5	40	150	μА
IS <sub>ON</sub>	Supply VS Current	VLI, VTX = 0V		3.5	10	mA
		$V_{CC} = 0.5V$ @ $V_S \le 12V$ 3)		<1	50	μΑ
IS <sub>SB</sub>		$V_{CC}$ = 0.5V, see fig. 5 @ $V_S \le 16V$			100	μА
VK <sub>low</sub>	Input Voltage LOW State	RX output status LOW	-24		0.40VS	V
$VK_{high}$	Input Voltage HIGH State	RX output status HIGH	0.60VS		VS	V
VK <sub>hys</sub>	Input Threshold Hysteresis	$ \begin{array}{l} VK_{high} - VK_{low} \\ V_S \geq 8.0V \\ V_S \geq 6.0V \end{array} $	0.2 0.08	0.05VS	1.0	V V
IK <sub>OFF</sub>	Input Current	$ \begin{array}{l} VTX \geq VTX_{high} \\ V_S, \ V_{CC} \geq 0V \ or \ V_S, \\ V_{CC} = open \ or \ GND = open \end{array} $	-5	4	40	μА
RK <sub>ON</sub>	Output ON Impedance			10	30	Ω
IK <sub>SC</sub>	Short Circuit Current	V <sub>S</sub> ≥ 6.5V	40	60	150	mA
VK <sub>sat</sub>	Output Saturation Voltage	$R_{KO} = 1.5K\Omega$			1	V
VTX <sub>low</sub>	Input Voltage LOW State		-24		1	V
VTX <sub>high</sub>	Input Voltage HIGH State		3.5		VCC	V
RRX <sub>ON</sub> RLO <sub>ON</sub>	Output ON Impedance	$ \begin{array}{l} VK \leq VK_{low}; \ \ VLI \leq VLI_{low} \\ V_S \geq 6.5V; \ \ I_{RX,LO} \geq 1mA \end{array} $		40	90	Ω
VRX <sub>sat</sub> VLO <sub>sat</sub>	Saturation Output Voltage	No external load			1	V
IRX <sub>SC</sub> ILO <sub>SC</sub>	Output short circuit current	V <sub>S</sub> ≥ 6.5V	9	20	50	mA
RTX	Input pull up resistance	$\begin{aligned} &\text{Output status} = (\text{HIGH}) \\ &T_{\text{A}} \leq 85^{\circ}\text{C} \\ &-0.15\text{V} \leq \text{VLO} \leq \text{VCC} + 0.15\text{V} \\ &-0.15\text{V} \leq \text{VRX} \leq \text{VCC} + 0.15\text{V} \end{aligned}$	5	10	18	kΩ
RTX	Input pull up resistance	$-0.15V \le VTX \le VCC + 0.15V$ $T_{amb} \le 125^{\circ}C$	10	20	40	kΩ
VLI <sub>low</sub>	Input voltage LOW state	LO output status LOW	-24		0.40VS	V
VLI <sub>high</sub>	Input voltage HIGH state	LO output status HIGH	0.60VS		VS	V
ILI	Input current	VS, VCC ≥ 0V or VS, VCC = open or GND = open	-5	4	40	μΑ

Note 1) For external supplied output currents lower than this value a series protection diode can become active. See also Fig. 4 and 5.

#### **ELECTRICAL CHARACTERISTICS** (continued)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
$C_{KI,LO,RX}$	Internal output capacities				20	pF
f <sub>LI-LO</sub> f <sub>K-RX</sub> f <sub>TX-K</sub>	Transmission frequency	$\begin{array}{l} 9V < V_S < 16V,\\ \text{(external loads)}\\ T_{min} \geq 20 \cdot R_{KO} \cdot C_K \cdot K_{line} \end{array}$	130			kHz
f <sub>LI-LO</sub> f <sub>K-RX</sub> f <sub>TX-K</sub>	Rise Time	for the definition of tr, tf see FIG. 1, 2)		0.4	2	μs
	Fall Time	$9V < V_S < 16V$ , (external loads) $T_{min} \ge 20 \cdot R_{KO} \cdot C_K - K_{line}$		0.4	2	μs
toff,Li-LO toff,K-RX toff,TX-K	Switch OFF time	for the definition of tr, tf see FIG. 1		1.3	3	μs
t <sub>ON,LI-LO</sub> t <sub>ON,K-RX</sub> t <sub>ON,TX-K</sub>	Switch ON time	$9V < V_S < 16V$ , (external loads) Tmin $\geq 20 \cdot R_{KO} \cdot C_K \cdot K_{line}$		1.3	3	μs
td <sub>SB ON</sub>	Standby reaction time	VTX = 0V, IK ≥ 7mA VLI = 0V, 9V < VS < 16V		10	20	μs
td <sub>SB OFF</sub>		see FIG. 2		20	40	μs

Note 2) Speed limitation related to external capacitance  $C_{\text{ext}\,\text{RX, LO}}$  and internal impedance  $C_{\text{LO, RX}}$ , RLO, RRX for rise time.  $t_r = R_{\text{LO, RX}} + C_{\text{ext}\,\text{RX, LO}} \cdot 1.38$ .

Note 3) In case of spikes on VCC ≥ 0.5V KOUT will be switched On for typical 10μs which represents the standby tdsB reaction time.

#### **FUNCTIONAL DESCRIPTION**

The L9613B is a monolithic bus driver designed to provide bidirectional serial communication in automotive applications.

The device provides a bidirectional link, called K, to the  $V_{Bat}$  related diagnosis bus. It also includes a separate comparator L which is also able to be linked to the  $V_{Bat}$  bus. The input TX and output RX of K are related to VCC with her integrated pull up resistances. Also the L comparator output LO has a pull up resistance connected to VCC.

All VBat bus defined inputs LI and K have supply voltage dependent thresholds together with sufficent hysteresis to suppress line spikes. These pins are protected against overvoltages, shorts to GND and VS and can also be driven beyond VS and GND. These features are also given for TX, RX and LI only taking into account the behaviour of the internal pull up resistances. The thermal shut down function switches OFF the K output if the chip temperature increases above the thermal shut down threshold. To reactivate K again the chip temperature must decrease below the K switch ON temp. To achieve no fault for VS undervoltage conditions the outputs will be switched OFF and stay at high impedance. The device is also protected against reverse battery condition. During lack of VS or GND all pins shows high impedance characteristic. To realize a lack of the VS related bus line LI and K the outputs LO and RX shows defined ON status. Supressing all 4 classes of "Schaffner" signals (Schaffner 1; 2; 3a,b; 4) all pins can be load with short energy pulses of max.  $\pm 0.2$ mJ. All these features together with a high possible baud rate >130Kbaud, controlled output slopes for low EMI, a wide power supply voltage range and a real standby function with zero power consumption ISsB typ  $\leq 1\mu$ A during system depowering VCC  $\leq 0.5$ V make this device high efficient for automotive bus system.

After wake up of the system from SB condition the first output signal will have an additional delay time  $td_{typ} \le 5\mu s$ .

The typical output voltage behaviour for the K, LO, RX outputs as a function of the output current is shown in Fig.5. Fig.6 shows a waveform of the output signal when the low level changes from  $R_{ON} \cdot I_{OUT}$  to  $I_{OUT} \cdot 2 \cdot R_{ON} + U_{BE}$  state. This variation occurs due to too low output current or after a negative transient forced to the output or to the supply voltage line.

V<sub>IN</sub>

Figure 1. Input to output timings and output pulse shape

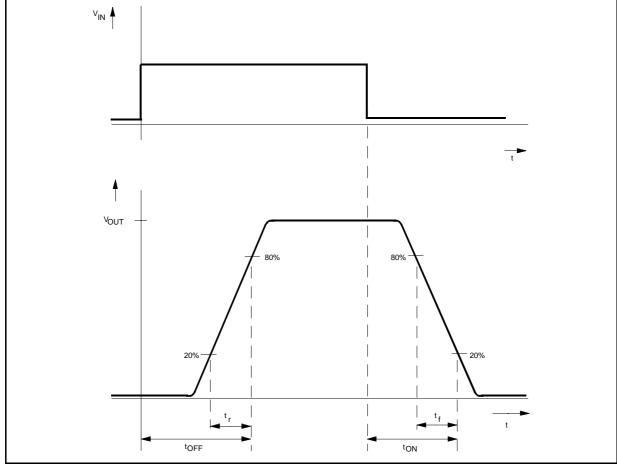


Figure 2. Standby reaction time.

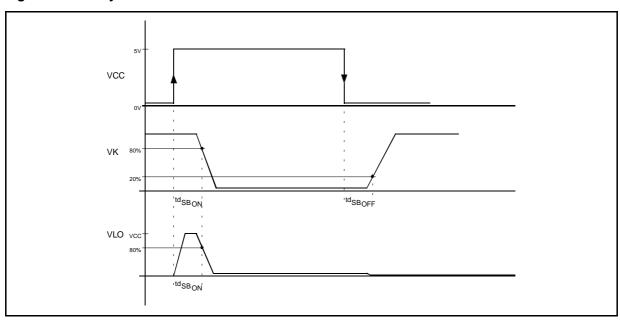


Figure 3. Output characteristics at K, LO, RX.

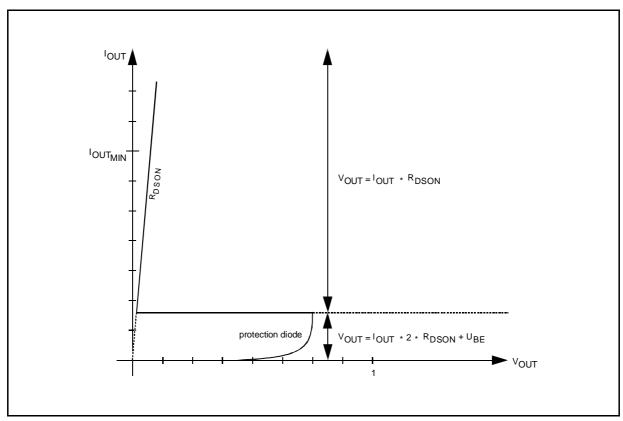
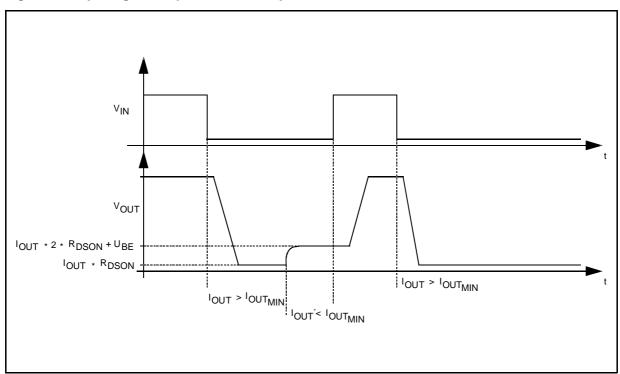


Figure 4. Output signal shape related to output current.



4

Figure 5. Standby current consumption.

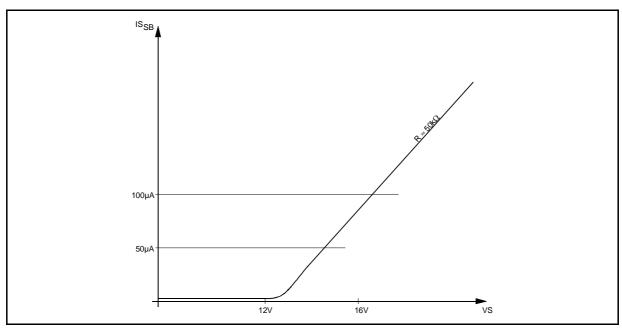
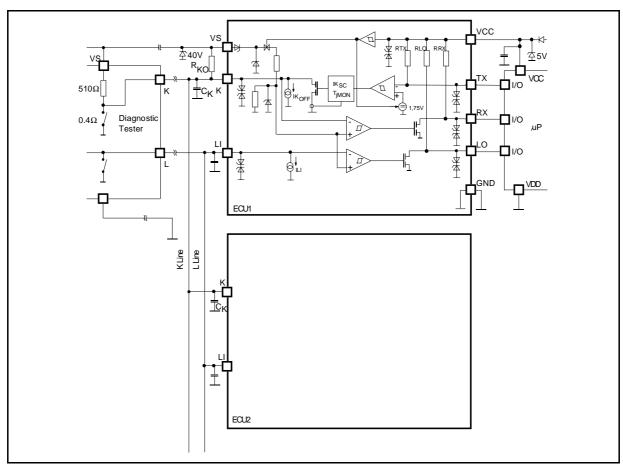


Figure 6. Application Circuit.



#### EMS Performance (ISO 9141 BUS system)

Figure 7.

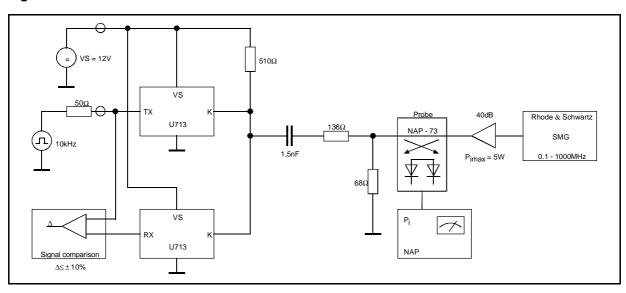
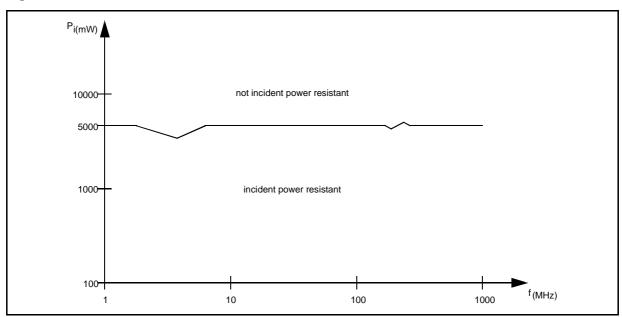


Figure 8.

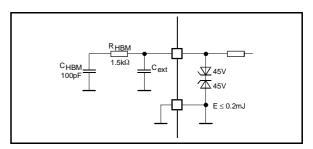


#### **ESD** application hints

To improve the ESD robustness of this device above specified  $\pm 2 \text{KV/HBM}$  external blocking capacitors must be used. Nevertheless the max. energy which can be clamped by this device should not exceeds 0.2mJ for each pin. An equivalent input diagram for calculation can be seen in fig. 9.

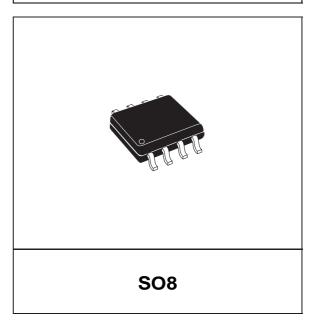
ESD duscharge model
$$E_{ESD} = \frac{1}{2} C_{HBM} U_{ESD}^2 = 0.2 \text{mJ} + \frac{1}{2} C_{EXT} \cdot (45 \text{V})^2$$

Figure 9.

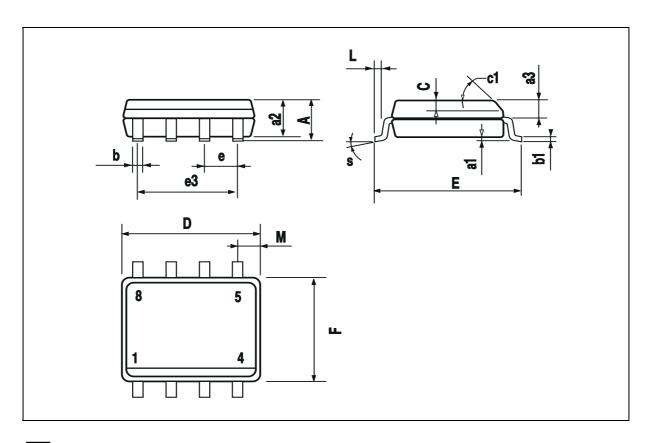


DIM.		mm			inch	
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
аЗ	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
С	0.25		0.5	0.010		0.020
c1			45° (	(typ.)		
D (1)	4.8		5.0	0.189		0.197
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
еЗ		3.81			0.150	
F (1)	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
М			0.6			0.024
S	8° (max.)					

# OUTLINE AND MECHANICAL DATA



<sup>(1)</sup> D and F do not include mold flash or protrusions. Mold flash or potrusions shall not exceed 0.15mm (.006inch).



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